

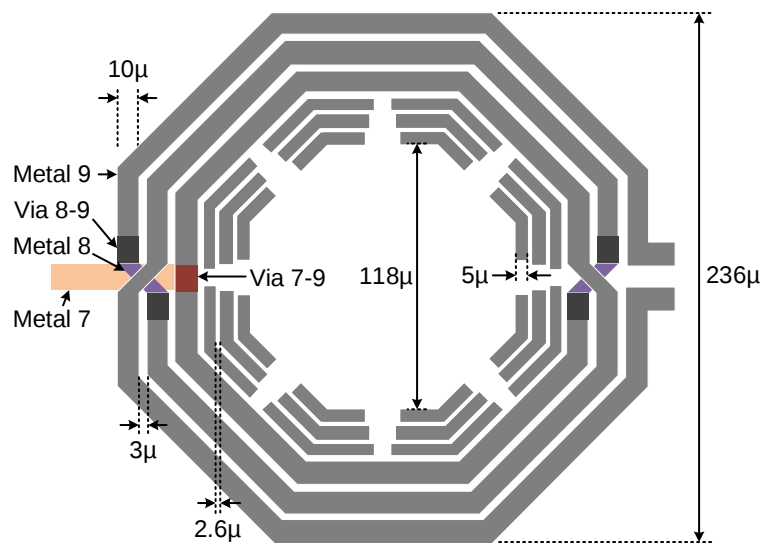
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# A CMOS-integrated quantum sensor based on nitrogen-vacancy centres

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Supplementary Figure 1. **Loop Inductor Design.**